MPSA42, MPSA43

MPSA42 is a Preferred Device

High Voltage Transistors

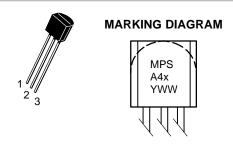
NPN Silicon



ON Semiconductor[™]

http://onsemi.com

COLLECTOR 3 2 BASE EMITTER



MPSA4x= Specific Device Code = 2 or 3 х

Υ = Year W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MPSA42	TO-92	5000 Units/Box
MPSA42RLRA	TO-92	2000/Tape & Reel
MPSA42RLRE	TO-92	2000/Tape & Reel
MPSA42RLRF	TO-92	5000 Units/Box
MPSA42RLRM	TO-92	2000/Ammo Pack
MPSA42RLRP	TO-92	2000/Ammo Pack
MPSA43	TO-92	5000 Units/Box
MPSA43RLRA	TO-92	2000/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MPSA43 MPSA42	V _{CEO}	200 300	Vdc
Collector–Base Voltage MPSA43 MPSA42	V _{CBO}	200 300	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	۱ _C	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

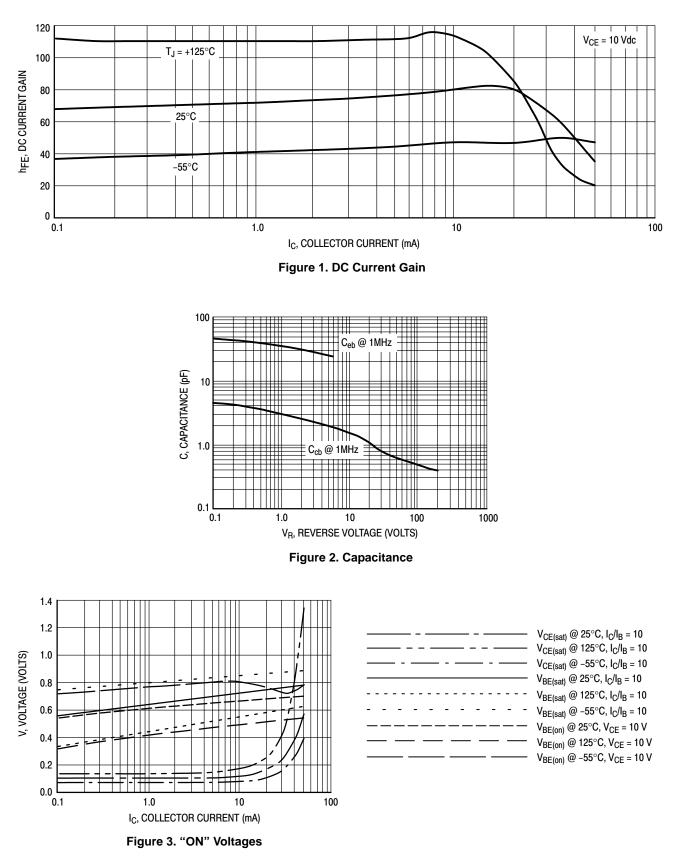
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R_{\thetaJA}	200	°C/mW
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/mW

MPSA42, MPSA43

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

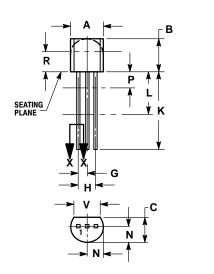
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (Note 1.) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	MPSA42 MPSA43	V _{(BR)CEO}	300 200		Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	MPSA42 MPSA43	V _{(BR)CBO}	300 200		Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \ \mu Adc, I_C = 0$)		V _{(BR)EBO}	6.0	-	Vdc
Collector Cutoff Current ($V_{CB} = 200 \text{ Vdc}, I_E = 0$) ($V_{CB} = 160 \text{ Vdc}, I_E = 0$)	MPSA42 MPSA43	I _{CBO}		0.1 0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$) ($V_{EB} = 4.0 \text{ Vdc}, I_C = 0$)	MPSA42 MPSA43	I _{EBO}	-	0.1 0.1	μAdc
ON CHARACTERISTICS (Note 1.)					
$ DC Current Gain \\ (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 10 mAdc, V_{CE} = 10 Vdc) \\ (I_C = 30 mAdc, V_{CE} = 10 Vdc) $		h _{FE}	25 40 40		-
Collector–Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	MPSA42 MPSA43	V _{CE(sat)}		0.5 0.4	Vdc
Base–Emitter Saturation Voltage $(I_C = 20 \text{ mAdc}, I_B = 2.0 \text{ mAdc})$		V _{BE(sat)}	-	0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS		4		ł	ł
Current–Gain – Bandwidth Product ($I_C = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)		f _T	50	-	MHz
Collector–Base Capacitance ($V_{CB} = 20 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	MPSA42 MPSA43	C _{cb}		3.0 4.0	pF

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.



PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**





NOTES:

DIMENSIONING AND TOLERANCING PER ANSI 1.

2.

CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 3 IS UNCONTROLLED.

LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM. 4.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1: STYLE 14: PIN 1. EMITTER PIN 1. EMITTER COLLECTOR 2. BASE 2. COLLECTOR 3. 3 BASE

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